



JMD70KD18T1W

Diode Module

Features

Parameter	Value	Unit
V_{RRM}	1800	V
$I_{F(AV)}(@ T_C = 100^\circ C)$	70	A

Absolute Maximum Ratings (@ $T_C = 25^\circ C$ unless otherwise specified)

Parameter	Conditions	Symbol	Values	Unit
Repetitive peak reverse voltage	$T_{vj} = 25^\circ C$	V_{RRM}	1800	V
Non-repetitive peak reverse voltage	$T_{vj} = 25^\circ C$	V_{RSM}	1900	V
Average forward current	$T_C = 100^\circ C$	$I_{F(AV)}$	70	A
Forward surge current	1/2 cycle, Sine wave, 50Hz	I_{FSM}	1960	A
I^2t value for fusing	$T_{vj} = 25$	I^2t	19200	A^2s
RMS isolation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3600/3000	V
Junction temperature range		T_J	-40 ~ +150	
Storage temperature range		T_{stg}	-40 ~ +125	

**Electrical Characteristics** (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Conditions	Symbol	Values	Unit

Typical Electrical & Thermal Characteristics

FIG.1: Forward characteristics(per diode)

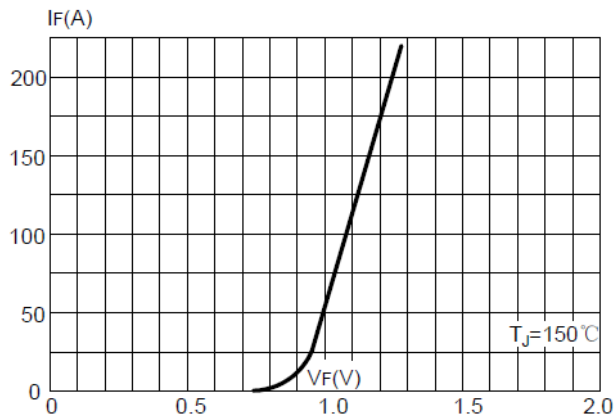
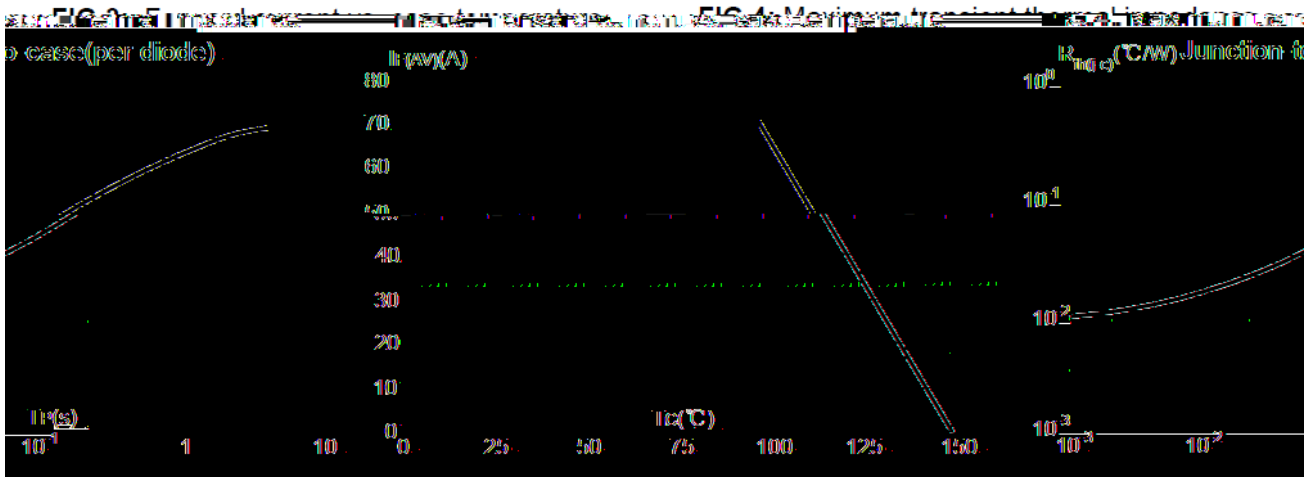
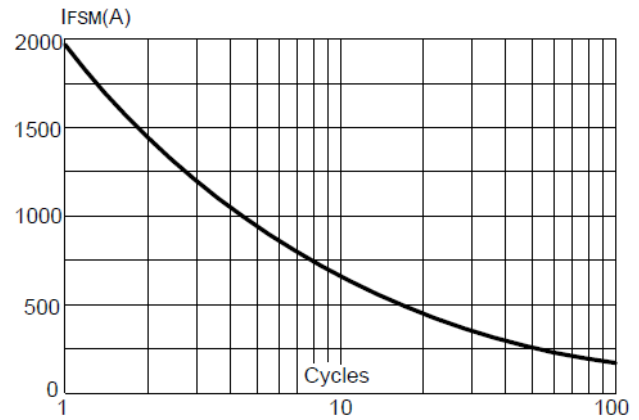
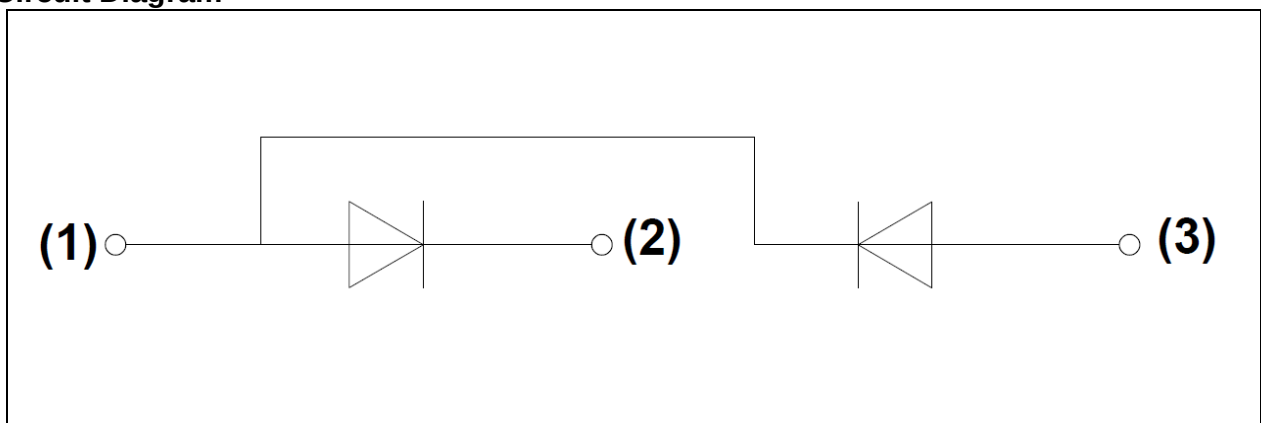


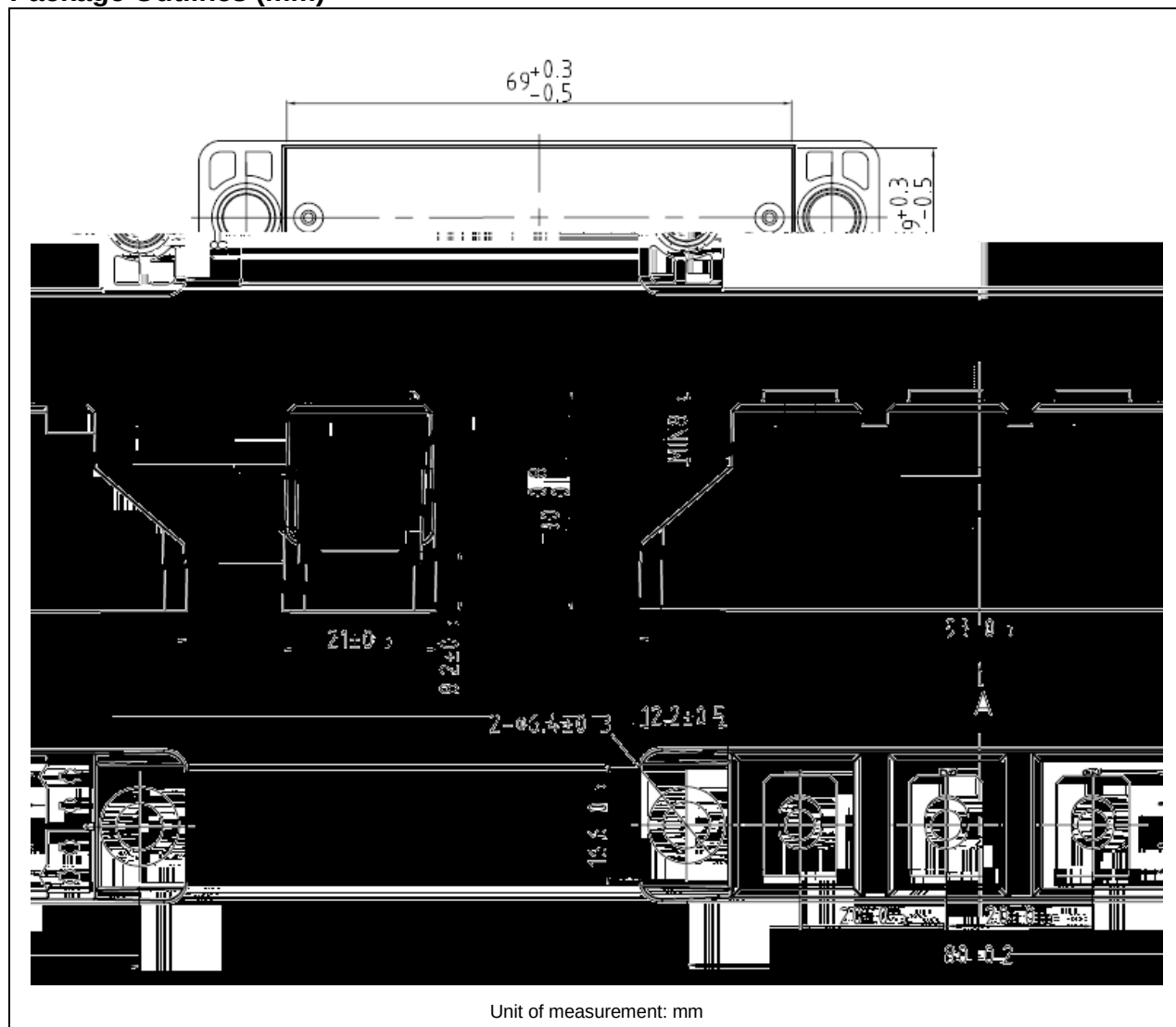
FIG.2: Peak on-state surge current



Circuit Diagram



Package Outlines (mm)





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